

# ZXTP07012EFF 12V, SOT23F, PNP medium power transistor

## Summary;

 $BV_{CEO} > -12V$ 

 $I_{C(cont)} = -4A$ 

 $V_{CE(sat)} < -75mV @ 1A$ 

 $R_{CE(sat)} = 50 m\Omega$ 

 $P_{D} = 1.5W$ 

Complementary part number ZXTN07012EFF

## **Description**

This low voltage PNP transistor has been designed for applications requiring high gain and very low saturation voltage. The SOT23F package is pin compatible with the industry standard SOT23 footprint but offers lower profile and higher dissipation for applications where power density is of utmost importance.

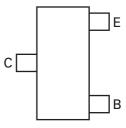
# B C

## **Features**

- Low profile SOT23F package
- · Low saturation voltage
- · High gain
- · High power dissipation

## **Applications**

- · Load switches
- · Battery charging
- Motor drive



Pinout - top view

## **Ordering information**

Device	Reel size	Tape width	Quantity	
	(inches)	(mm)	per reel	
ZXTP07012EFFTA	7	8	3000	

## **Device marking**

1D1

# **Absolute maximum ratings**

Parameter	Symbol	Limit	Unit
Collector-base voltage	V <sub>CBO</sub>	-12	V
Collector-emitter voltage	V <sub>CEO</sub>	-12	V
Emitter-base voltage	V <sub>EBO</sub>	-7	V
Continuous collector current <sup>(c)</sup>	I <sub>C</sub>	-4	Α
Peak pulse current	I <sub>CM</sub>	-8	Α
Base current	I <sub>B</sub>	-1	Α
Power dissipation at T <sub>amb</sub> =25°C <sup>(a)</sup>		0.84	W
Linear derating factor	$P_{D}$	6.72	mW/°C
Power dissipation at T <sub>amb</sub> =25°C <sup>(b)</sup>		1.34	W
Linear derating factor	$P_{D}$	10.72	mW/°C
Power dissipation at T <sub>amb</sub> =25°C <sup>(c)</sup>		1.50	W
Linear derating factor	$P_{D}$	12.0	mW/°C
Power dissipation at T <sub>amb</sub> =25°C <sup>(d)</sup>		2.0	W
Linear derating factor	$P_{D}$	16.0	mW/°C
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	°C

## Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	149	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\Theta JA}$	93	°C/W
Junction to ambient <sup>(c)</sup>	$R_{\Theta JA}$	83	°C/W
Junction to ambient <sup>(d)</sup>	$R_{\Theta JA}$	60	°C/W

#### NOTES:

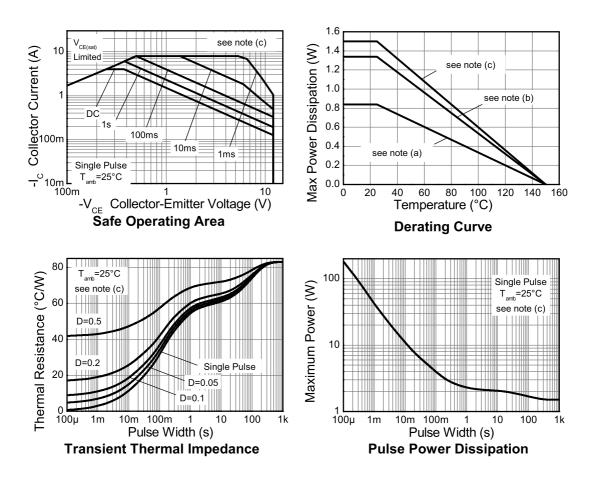
<sup>(</sup>a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

<sup>(</sup>b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

<sup>(</sup>c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

<sup>(</sup>d) As (c) above measured at t<5secs.

## **Characteristics**



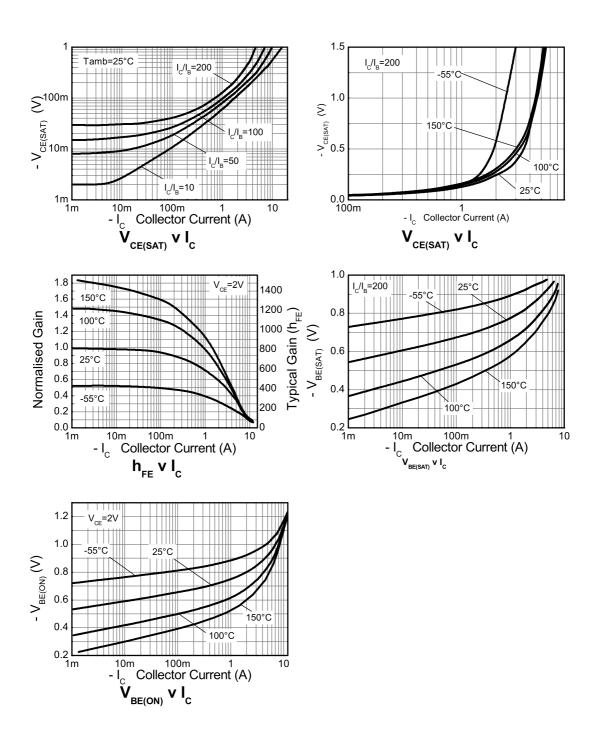
# Electrical characteristics (at $T_{amb} = 25$ °C unless otherwise stated)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CBO</sub>	-12	-23		V	I <sub>C</sub> = -100μA
Collector-emitter breakdown voltage (base open)	BV <sub>CEO</sub>	-12	-16		V	I <sub>C</sub> = -10mA <sup>(*)</sup> *
Emitter-base breakdown voltage	BV <sub>EBO</sub>	-7	-8.4		V	I <sub>E</sub> = -100μA
Collector-base cut-off current	I <sub>CBO</sub>		<-1	-50	nA	V <sub>CB</sub> = -10V
				-20	μΑ	$V_{CB} = -10V, T_{amb} = 100^{\circ}C$
Emitter-base cut-off current	I <sub>EBO</sub>		<-1	-50	nA	V <sub>EB</sub> = -5.6V
Collector-emitter saturation	V <sub>CE(sat)</sub>		-80	-100	mV	$I_C = -0.5A$ , $I_B = -2.5mA^{(*)}$
voltage			-60	-75	mV	$I_C = -1A$ , $I_B = -100 \text{mA}^{(*)}$
			-130	-165	mV	$I_C = -1A$ , $I_B = -5mA^{(*)}$
			-250	-350	mV	$I_C = -2A$ , $I_B = -10mA^{(*)}$
			-260	-340	mV	$I_C = -4A$ , $I_B = -80 \text{mA}^{(*)}$
Base-emitter saturation voltage	V <sub>BE(sat)</sub>		-945	-1050	mV	$I_C = -4A$ , $I_B = -80 \text{mA}^{(*)}$
Base-emitter turn-on voltage	V <sub>BE(on)</sub>		-850	-950	mV	$I_C = -4A$ , $V_{CE} = -2V^{(*)}$
Static forward current	h <sub>FE</sub>	500	750	1500		$I_C = -10 \text{mA}, V_{CE} = -2V^{(*)}$
transfer ratio		400	570			$I_C = -1A, V_{CE} = -2V^{(*)}$
		230	320			$I_C = -4A$ , $V_{CE} = -2V^{(*)}$
		150	210			$I_C = -6A$ , $V_{CE} = -2V^{(*)}$
Transition frequency	f <sub>T</sub>	100	250		MHz	$I_C = -50 \text{mA}, V_{CE} = -5V$ f = 50MHz
Input capacitance	C <sub>ibo</sub>		223		pF	$V_{CB} = -0.5V, f = 1MHz^{(*)}$
Output capacitance	C <sub>obo</sub>		49	60	pF	V <sub>CB</sub> = -8V, f = 1MHz <sup>(*)</sup>
Delay time	t <sub>d</sub>		12.8		ns	V <sub>CC</sub> = -10V.
Rise time	t <sub>r</sub>		15.6		ns	$I_{C} = -500 \text{mA},$
Storage time	t <sub>s</sub>		240		ns	$I_{B1} = I_{B2} = -50 \text{mA}.$
Fall time	t <sub>f</sub>		92.8		ns	

#### NOTES

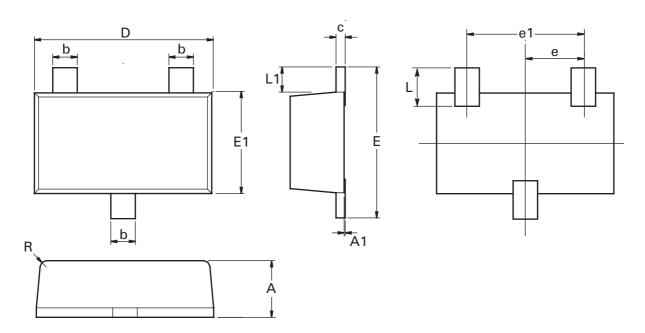
<sup>(\*)</sup> Measured under pulsed conditions. Pulse width  ${\leq}300\mu s;$  duty cycle  ${\leq}2\%.$ 

# **Typical characteristics**



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# Package outline - SOT23F



Dim.	Millim	neters	Inc	hes	Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
Α	0.80	1.00	0.0315	0.0394	Е	2.30	2.50	0.0906	0.0984
A1	0.00	0.10	0.00	0.0043	E1	1.50	1.70	0.0590	0.0669
b	0.35	0.45	0.0153	0.0161	E2	1.10	1.26	0.0433	0.0496
С	0.10	0.20	0.0043	0.0079	L	0.48	0.68	0.0189	0.0268
D	2.80	3.00	0.1102	0.1181	L1	0.30	0.50	0.0153	0.0161
е	0.95	ref	0.037	74 ref	R	0.05	0.15	0.0019	0.0059
e1	1.80	2.00	0.0709	0.0787	0	0°	12°	0°	12°

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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